

**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ/T 1486-2016

Replacing SJ 1486-1979

**Discrete semiconductor devices 3CG180 silicon PNP frequency
high power transistor backpressure small detail specification**

半导体分立器件 3CG180型硅PNP高频高反压小功率晶体管详细规范

(English Translation)

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What this standard covers

This standard specifies the external dimensions, maximum ratings and electrical characteristics, test conditions and inspection requirements of 3CG180 silicon PNP high frequency high back pressure small power transistor devices.

Document data

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